

UNISONIC TECHNOLOGIES CO., LTD

6NM95 **Preliminary Power MOSFET**

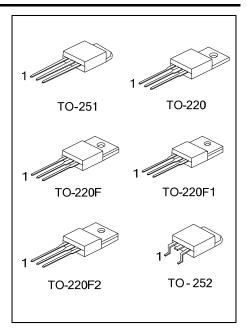
6.0A, 950V N-CHANNEL **SUPER-JUNCTION MOSFET**

DESCRIPTION

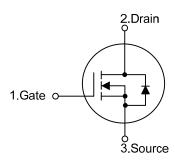
The UTC 6NM95 is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(on)}$ < 1.9 Ω @ V_{GS} =10V, I_{D} =3.0A
- * Improved dv/dt capability
- * Fast switching
- * 100% avalanche tested



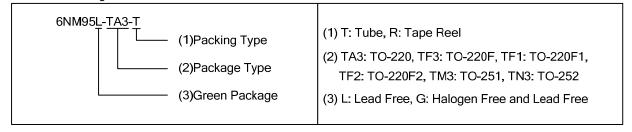
SYMBOL



ORDERING INFORMATION

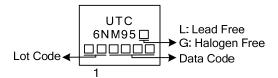
Ordering Number		D. J	Pin Assignment			5 1.	
Lead Free	Halogen Free	Package	1	2	3	Packing	
6NM95L-TA3-T	6NM95G-TA3-T	TO-220	G	D	S	Tube	
6NM95L-TF3-T	6NM95G-TF3-T	TO-220F	G	D	S	Tube	
6NM95L-TF1-T	6NM95G-TF1-T	TO-220F1	G	D	S	Tube	
6NM95L-TF2-T	6NM95G-TF2-T	TO-220F2	G	D	S	Tube	
6NM95L-TM3-T	6NM95G-TM3-T	TO-251	G	D	S	Tube	
6NM95L-TN3-R	6NM95G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	950	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_{D}	6.0	Α
Pulsed Drain Current (Note 2)		I _{DM}	24	Α
Avalanche Current (Note 2)		I _{AR}	3.0	Α
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	45	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.56	V/ns
Power Dissipation	TO-220		132	W
	TO-220F/TO-220F1 TO-220F2	P_D	56	W
	TO-251/TO-252		60	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature
- 3. L = 10mH, I_{AS} = 3.0A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 4. $I_{SD} \le 6.0$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25$ °C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction-to-Ambient	TO-220/TO-220F TO-220F1/ TO-220F2	θја	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction-to-Case	TO-220	θјс	0.95	°C/W
	TO-220F/TO-220F1 TO-220F2		2.23	°C/W
	TO-251/TO-252		2.08	°C/W

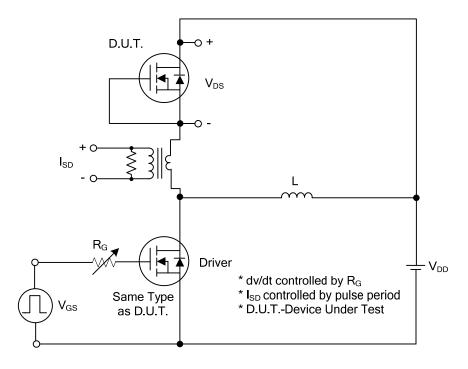
■ **ELECTRICAL CHARACTERISTICS** (T_C =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_D = 250\mu A$				V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 950V, V _{GS} = 0V			10	μA		
Cata Sauraa Laakaga Currant	I _{GSS}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA		
Gate-Source Leakage Current		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.5	V		
Static Drain-Source On-State Resistance	R _{DS(ON)}	$V_{GS} = 10V, I_D = 3.0A$			1.9	Ω		
DYNAMIC CHARACTERISTICS								
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		500		pF		
Output Capacitance	Coss			165		pF		
Reverse Transfer Capacitance	C_{RSS}			7.0		pF		
SWITCHING CHARACTERISTICS								
Total Gate Charge (Note 1)	Q_G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A , -I _G =100μA (Note 1, 2)		50		nC		
Gate to Source Charge	Q_GS			4.5		nC		
Gate to Drain Charge	Q_GD			14.5		nC		
Turn-ON Delay Time (Note 1)	t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A,		50		nS		
Rise Time	t_R			85		nS		
Turn-OFF Delay Time	t _{D(OFF)}	R _G =25Ω (Note 1, 2)		220		nS		
Fall-Time	t _F			48		nS		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current	I _S				6	Α		
Maximum Body-Diode Pulsed Current	I _{SM}				24	Α		
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I _S =6.0A, V _{GS} =0V			1.4	V		
Body Diode Reverse Recovery Time (Note 1)	t _{rr}	I _S =6.0A, V _{GS} =0V,		525		nS		
Body Diode Reverse Recovery Charge	Q_{rr}	dI _F /dt =100A/μs		5.6		μC		

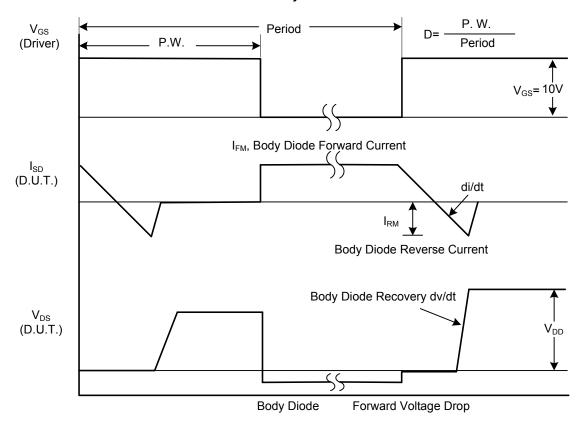
Notes: 1. Pulse Test : Pulse width ≤300µs, Duty cycle ≤2%.

^{2.} Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

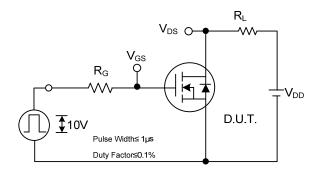


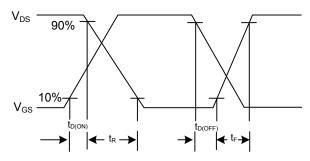
Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

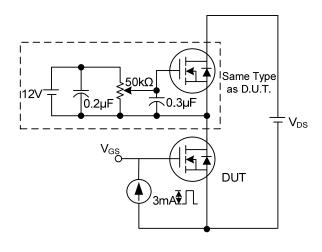
■ TEST CIRCUITS AND WAVEFORMS (Cont.)

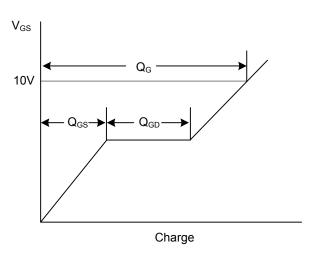




Switching Test Circuit

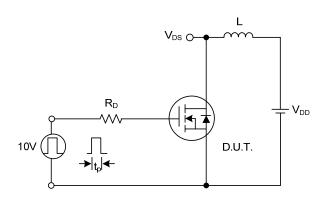
Switching Waveforms

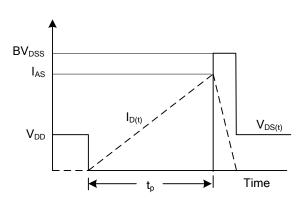




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

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